AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph at page 1, lines 6-11 as follows:

Technical Field ~~of the Invention~~

~~The present invention relates to a~~ A method of forming an isolation film in a semiconductor device is disclosed~~, and more particularly, to a method of forming an isolation film in a semiconductor device~~ which is capable of preventing concentration of an electric field on the top corners of the trench in the isolation film of a STI (shallow trench isolation) structure.

Please amend the paragraphs at page 3, line 19 to page 4, line 20 as follows:

SUMMARY OF THE ~~INVENTION~~ DISCLOSURE

Accordingly, the ~~present invention is~~ techniques disclosed herein have been contrived to substantially obviate one or more problems due to limitations and disadvantages of the related art.

~~An object of the present invention is to provide a~~ One disclosed method of forming an isolation film in a semiconductor device comprises, in the process of forming a stack structure of a pad oxide film and a pad nitride film that expose a semiconductor substrate in an isolation region, forming protrusions of a tail profile at the bottom sidewalls of the pad nitride film and the pad oxide film adjacent to the surface of the substrate and making rounded the top corners of a trench using the protrusions as an anti-etch film when the semiconductor substrate is etched, whereby concentration of an electric field on the top corners of the trench is prevented and generation of the leakage current is prohibited, thus improving reliability of the process and electrical characteristics of the device and simultaneously solving a difficult of the process for polymer since the top corners of the trench is made rounded even with the photoresist pattern removed.

Additional advantages~~, objects,~~ and features ~~of the invention~~ will be set forth in part in the description which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of the invention. ~~The objectives and other~~ Other advantages ~~of the invention~~ may be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

~~To achieve these objects and other advantages and in accordance with the purpose of the invention, as embodied and broadly described herein, a~~ Another method of forming an isolation film in a semiconductor device according to a preferred embodiment ~~of the present invention~~ is characterized in that it comprises the steps of sequentially forming a pad oxide film and a pad nitride film on a semiconductor substrate, removing the pad nitride film and the pad oxide film on an isolation region so that protrusions of a tail profile are formed at the top corners of the isolation region, etching the semiconductor substrate of the isolation region, while using the protrusions as an anti-etch film, to form a trench the top corners of which are made rounded, and burying the trench with an insulating material and then removing the pad nitride film and the pad oxide film on the semiconductor substrate to form an isolation film.

Please amend the paragraphs at page 5, line 27 to page 6, line 13 as follows:

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other ~~objects,~~ features and advantages of the ~~present invention~~ will be apparent from the following detailed description of the preferred embodiments of the invention in conjunction with the accompanying drawings, ~~in which~~ wherein:

FIG. 1A ~ FIG. 1D are cross-sectional views of the semiconductor devices for explaining a conventional method of forming an isolation film in the semiconductor device;

FIG. 2A ~ FIG. 2E are cross-sectional views of the semiconductor devices for explaining a disclosed method of forming an isolation film in the semiconductor device ~~a preferred embodiment of the present invention~~; and

FIG. 3A and FIG. 3B are cross-sectional views of the semiconductor devices for explaining an embodiment of the etch process for forming the trench as shown in FIG. 2C.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT

Reference will now be made in detail to the preferred embodiments ~~of the present invention~~, examples of which are illustrated in the accompanying drawings, in which like reference numerals are used to identify the same or similar parts.

Please amend the paragraph at page 9, lines 19-23 as follows:

At this time, one of the most important characteristics ~~of the present invention why~~ the trench is formed by the above method, is as follows. As the trench is formed with the photoresist pattern removed, the trench is not affected by polymer occurring from the photoresist. Therefore, the etch process could be more accurately controlled and reliability of the process can be thus improved.